

HIGH ENERGY ESD STRUCTURE AND METHOD

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Abstract of the Disclosure

In one embodiment, a concentric ring ESD structure includes a first p-type region and a second p-type region are formed in a layer of semiconductor material. The two p-type regions are
10 coupled together with a floating n-type buried layer. The first and second p-type regions form a back-to-back diode structure with the floating n-type buried layer. A pair of shorted n-type and p-type contact regions is formed in each of the first and
15 second regions. An isolation region is formed between the first and second p-type regions.